Synthesis of Twisted Carbon Nanofiber by Catalytic CVD Method

Takashi Katsumata, Youhei Fujimura, Makoto Nagayama, Hiroshi Tabata, Hirofumi Takikawa, Yoshihiko Hibi, Tateki Sakakibara, Shigeo Itoh* Department of Electrical and Electronic Engineering, Toyohashi University of Technology, Toyohashi, 441-8580 Japan, Fax: 81-0532-44-6727, e-mail: takikawa@eee.tut.ac.jp

Product Development Center, Futaba Corporation, Japan

Helical carbon nanofibers (HCNF) were synthesized by the catalytic CVD method. The catalyst was a compound comprised of nickel (Ni) and copper (Cu), or their oxides, in the form of a multi-layer or mixture-layer film. They were prepared on a quartz substrate by physical vapor deposition (PVD) and sol-gel drop-coat methods. First, the dependence on source gas and dependence on presence/absence of a hot-filament assist were tested using Ni/Cu PVD film as a catalyst. The dilute gas used was helium (He). When acetylene (C₂H₂) gas was used, carbon nanocoils (CNCs) and carbon nanoropes (CNRs) were deposited without hot-filament assist and with assist, respectively. When ethylene (C₂H₄) gas was used with hot-filament assist, carbon nanotwists (CNTws) were deposited. Secondarily, the catalyst mixture of Ni oxide (NiO)/Cu oxide (CuO), prepared by the sol-gel drop-coat method, was tested for use with C₂H₂ gas. The influence of the mixing ratio of catalysts, process temperature, and the source/dilute gas ratio was examined. Optimum conditions for efficient HCNF synthesis were found to be as follows: NiO/CuO ratio, 2/8; process temperature, 500-600°C; C₂H₂/He flow rate ratio, 3/10 – 4/10. The obtained product in the latter experiment was mainly CNTw.

Keywords: helical carbon nanofiber, carbon nanotwist, catalytic CVD, Ni/Cu multi catalysts, optimization

1. INTRODUCTION

Since 1953, when carbon fiber with a helical structure was first reported [1,2], various types of chemical vapor deposition (CVD) methods have been developed, a variety of catalysts have been examined under various process conditions, and many carbon fiber growth models have been proposed. In 1990, Motojima et al. fabricated regular-coiled carbon fibers with high reproducibility [3]. They are referred to in review articles [4, 5]. Recently, helical, spiral, or twisted carbon fibers on an under-submicron scale, have been prepared by the CVD method with an ion (Fe) on indium-tin-oxide (ITO) film [6], and nickel (Ni) or zinc (Zn) on a copper (Cu) substrate [7-10]. Such helical carbon nanofibers (HCNFs) have field emission properties [9, 11], and are considered to be useful for various applications such as nano-springs, electric

Filament (NiCr) Substrate with catalyst

He C₂H₂ or C₂H₄

Bubbler

Fig. 1. Experimental setup of the catalytic CVD apparatus with hot-filament.

nano-inductors, electromagnetic shields, gas storage, fillers in polymers and various types of rubbers.

In the present paper, HCNFs were fabricated using a compound catalyst of nickel (Ni) and copper (Cu), or their oxides (NiO, CuO). First, various shapes of HCNFs were synthesized by a Ni/Cu multi-layer catalyst of thin solid film prepared by physical vapor deposition (PVD) using the vacuum arc plasma. Second, the influence of mixing ratios of catalysts, process temperatures, and the source/dilute gas ratio was examined using an NiO/CuO compound film prepared by the sol-gel drop-coat method.

2. EXPERIMENTAL DETAILS

Figure 1 shows the experimental setup of the catalytic CVD apparatus with a nickel-chromium alloy (NiCr) hot-filament. The electric furnace and the quartz tube process chamber were horizontally arranged. Source gases were acetylene (C2H2) and ethylene (C2H4). The dilute gas was helium (He). When the hot filament was turned on, the temperature was set at 1,000°C approximately 30 mm upstream from the substrate. The substrate was quartz measuring approximately 10×10 mm2 and 1 mm in thickness. The experimental procedure was as follows. After the catalyst-coated substrate was placed at the center of the quartz tube, the temperature of the electric furnace was increased from room temperature to the set temperature during approximately 1 hour with He gas flow of 420 ml/min. Then the source gas was introduced for 10 or 20 min with/without the hot filament assist. After the deposition process, the furnace was cooled down to the room temperature over approximately 1 hour with He gas flow